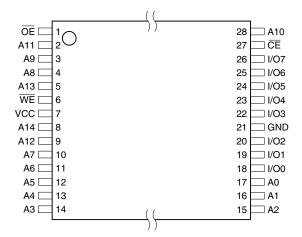


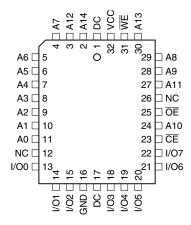
2. Pin Configurations

Pin Name	Function
A0 - A14	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
1/00 - 1/07	Data Inputs/Outputs
NC	No Connect
DC	Don't Connect

2.1 28-lead TSOP Top View



2.3 32-pad LCC, 28-lead PLCC Top View



Note: PLCC package pins 1 and 17 are Don't Connect.

2.2 28-lead PGA Top View

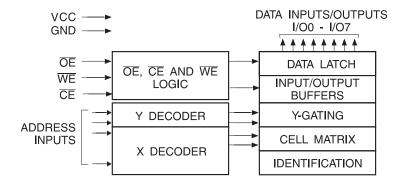
4	3	1	27	26
A6	A7	A14	WE	A13
5	2	28	24	25
A5	A12	VCC	A9	A8
7 A3	6 A4		22 OE	23 A11
9 A1	8 A2		20 CE	21 A10
11	10	14	16	19
I/O0	A0	GND	I/O4	I/O7
12	13	15	17	18
I/O1	I/O2	I/O3	I/O5	I/O6

2.4 28-lead Cerdip/PDIP/Flatpack/SOIC – Top View

A14 🗔	1	28	UCC
A12 🗀	2	27	□ WE
A7 🗀	3	26	A13
A6 🗀	4	25	□ A8
A5 🗀	5	24	□ A9
A4 🗔	6	23	A11
A3 🗔	7	22	□ ŌE
A2 🗀	8	21	A10
A1 🗔	9	20	□ CE
A0 🗀	10	19	□ I/O7
I/O0	11	18	□ I/O6
I/O1 🗀	12	17	□ I/O5
I/O2 🗀	13	16	□ I/O4
GND □	14	15	□ I/O3

2

3. Block Diagram



4. Device Operation

4.1 Read

The AT28C256 is accessed like a Static RAM. When $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are low and $\overline{\text{WE}}$ is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state when either $\overline{\text{CE}}$ or $\overline{\text{OE}}$ is high. This dual-line control gives designers flexibility in preventing bus contention in their system.

4.2 Byte Write

A low pulse on the $\overline{\text{WE}}$ or $\overline{\text{CE}}$ input with $\overline{\text{CE}}$ or $\overline{\text{WE}}$ low (respectively) and $\overline{\text{OE}}$ high initiates a write cycle. The address is latched on the falling edge of $\overline{\text{CE}}$ or $\overline{\text{WE}}$, whichever occurs last. The data is latched by the first rising edge of $\overline{\text{CE}}$ or $\overline{\text{WE}}$. Once a byte write has been started it will automatically time itself to completion. Once a programming operation has been initiated and for the duration of t_{WC} , a read operation will effectively be a polling operation.

4.3 Page Write

The page write operation of the AT28C256 allows 1 to 64 bytes of data to be written into the device during a single internal programming period. A page write operation is initiated in the same manner as a byte write; the first byte written can then be followed by 1 to 63 additional bytes. Each successive byte must be written within 150 μ s (t_{BLC}) of the previous byte. If the t_{BLC} limit is exceeded the AT28C256 will cease accepting data and commence the internal programming operation. All bytes during a page write operation must reside on the same page as defined by the state of the A6 - A14 inputs. For each \overline{WE} high to low transition during the page write operation, A6 - A14 must be the same.

The A0 to A5 inputs are used to specify which bytes within the page are to be written. The bytes may be loaded in any order and may be altered within the same load period. Only bytes which are specified for writing will be written; unnecessary cycling of other bytes within the page does not occur.

4.4 DATA Polling

The AT28C256 features \overline{DATA} Polling to indicate the end of a write cycle. During a byte or page write cycle an attempted read of the last byte written will result in the complement of the written data to be presented on I/O7. Once the write cycle has been completed, true data is valid on all outputs, and the next write cycle may begin. \overline{DATA} Polling may begin at anytime during the write cycle.





4.5 Toggle Bit

In addition to DATA Polling the AT28C256 provides another method for determining the end of a write cycle. During the write operation, successive attempts to read data from the device will result in I/O6 toggling between one and zero. Once the write has completed, I/O6 will stop toggling and valid data will be read. Reading the toggle bit may begin at any time during the write cycle.

4.6 Data Protection

If precautions are not taken, inadvertent writes may occur during transitions of the host system power supply. Atmel has incorporated both hardware and software features that will protect the memory against inadvertent writes.

4.6.1 Hardware Protection

Hardware features protect against inadvertent writes to the AT28C256 in the following ways: (a) V_{CC} sense – if V_{CC} is below 3.8V (typical) the write function is inhibited; (b) V_{CC} power-on delay – once V_{CC} has reached 3.8V the device will automatically time out 5 ms (typical) before allowing a write; (c) write inhibit – holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits write cycles; and (d) noise filter – pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a write cycle.

4.6.2 Software Data Protection

A software controlled data protection feature has been implemented on the AT28C256. When enabled, the software data protection (SDP), will prevent inadvertent writes. The SDP feature may be enabled or disabled by the user; the AT28C256 is shipped from Atmel with SDP disabled.

SDP is enabled by the host system issuing a series of three write commands; three specific bytes of data are written to three specific addresses (refer to "Software Data Protection" algorithm). After writing the 3-byte command sequence and after t_{WC} the entire AT28C256 will be protected against inadvertent write operations. It should be noted, that once protected the host may still perform a byte or page write to the AT28C256. This is done by preceding the data to be written by the same 3-byte command sequence used to enable SDP.

Once set, SDP will remain active unless the disable command sequence is issued. Power transitions do not disable SDP and SDP will protect the AT28C256 during power-up and power-down conditions. All command sequences must conform to the page write timing specifications. The data in the enable and disable command sequences is not written to the device and the memory addresses used in the sequence may be written with data in either a byte or page write operation.

After setting SDP, any attempt to write to the device without the 3-byte command sequence will start the internal write timers. No data will be written to the device; however, for the duration of t_{WC} , read operations will effectively be polling operations.

4.7 Device Identification

An extra 64 bytes of EEPROM memory are available to the user for device identification. By raising A9 to 12V \pm 0.5V and using address locations 7FC0H to 7FFFH the additional bytes may be written to or read from in the same manner as the regular memory array.

4.8 Optional Chip Erase Mode

The entire device can be erased using a 6-byte software code. Please see "Software Chip Erase" application note for details.

4 AT28C256

5. DC and AC Operating Range

		AT28C256-15	AT28C256-20	AT28C256-25	AT28C256-35
Operating Temperature	Ind.	-40°C - 85°C			
(Case)	Mil.	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C
V _{CC} Power Supply		5V ±10%	5V ±10%	5V ±10%	5V ±10%

6. Operating Modes

Mode	CE	ŌE	WE	I/O
Read	V _{IL}	V _{IL}	V _{IH}	D _{OUT}
Write ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	D _{IN}
Standby/Write Inhibit	V _{IH}	X ⁽¹⁾	Х	High Z
Write Inhibit	X	Х	V _{IH}	
Write Inhibit	Х	V _{IL}	Х	
Output Disable	Х	V _{IH}	Х	High Z
Chip Erase	V _{IL}	V _H ⁽³⁾	V _{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH}.

2. Refer to AC programming waveforms.

3. $V_H = 12.0V \pm 0.5V$.

7. Absolute Maximum Ratings*

Temperature under Bias55°C to +125°C
Storage Temperature65°C to +150°C
All Input Voltages (including NC Pins)
with Respect to Ground0.6V to +6.25V
All Output Voltages with Respect to Ground0.6V to $V_{\rm CC}$ + 0.6V
Voltage on $\overline{\text{OE}}$ and A9 with Respect to Ground0.6V to +13.5V

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

8. DC Characteristics

Symbol	Parameter	Condition		Min	Max	Units
ILI	Input Load Current	$V_{IN} = 0V \text{ to } V_{CC} + 1V$			10	μΑ
I _{LO}	Output Leakage Current	$V_{I/O} = 0V \text{ to } V_{CC}$			10	μΑ
	V Ctandby Current CMOC	$\overline{CE} = V_{CC} - 0.3V$ to $V_{CC} + 1V$	Ind.		200	μΑ
I _{SB1}	V _{CC} Standby Current CMOS		Mil.		300	μΑ
I _{SB2}	V _{CC} Standby Current TTL	$\overline{\text{CE}}$ = 2.0V to V _{CC} + 1V			3	mA
I _{CC}	V _{CC} Active Current	$f = 5 \text{ MHz}; I_{OUT} = 0 \text{ mA}$			50	mA
V _{IL}	Input Low Voltage				0.8	V
V _{IH}	Input High Voltage			2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA			0.45	V
V _{OH}	Output High Voltage	I _{OH} = -400 μA		2.4		V

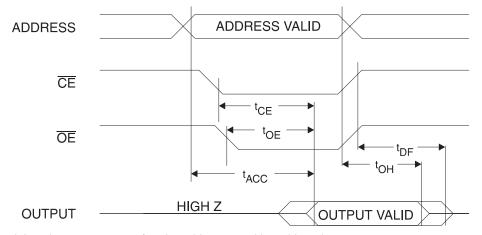




9. AC Read Characteristics

		AT28C256-15		AT28C256-20		AT28C256-25		AT28C256-35		
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	Units
t _{ACC}	Address to Output Delay		150		200		250		350	ns
t _{CE} ⁽¹⁾	CE to Output Delay		150		200		250		350	ns
t _{OE} ⁽²⁾	OE to Output Delay	0	70	0	80	0	100	0	100	ns
t _{DF} ⁽³⁾⁽⁴⁾	CE or OE to Output Float	0	50	0	55	0	60	0	70	ns
t _{OH}	Output Hold from \overline{OE} , \overline{CE} or Address, whichever occurred first	0		0		0		0		ns

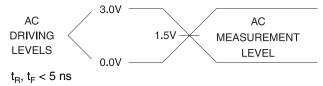
10. AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾



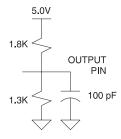
Notes: 1. $\overline{\text{CE}}$ may be delayed up to t_{ACC} - t_{CE} after the address transition without impact on t_{ACC} .

- 2. $\overline{\text{OE}}$ may be delayed up to t_{CE} t_{OE} after the falling edge of $\overline{\text{CE}}$ without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC} .
- 3. t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
- 4. This parameter is characterized and is not 100% tested.

11. Input Test Waveforms and Measurement Level



12. Output Test Load



13. Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$

Symbol	Тур	Max Units		Conditions
C _{IN}	4	6	pF	$V_{IN} = 0V$
C _{OUT}	8	12	pF	V _{OUT} = 0V

Note: 1. This parameter is characterized and is not 100% tested.





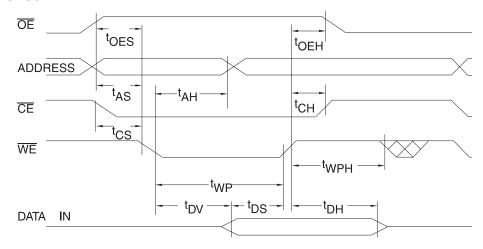
14. AC Write Characteristics

Symbol	Parameter	Min	Max	Units
t _{AS} , t _{OES}	Address, OE Setup Time	0		ns
t _{AH}	Address Hold Time	50		ns
t _{CS}	Chip Select Setup Time	0		ns
t _{CH}	Chip Select Hold Time	0		ns
t _{WP}	Write Pulse Width (WE or CE)	100		ns
t _{DS}	Data Setup Time	50		ns
t _{DH} , t _{OEH}	Data, $\overline{\text{OE}}$ Hold Time	0		ns
t _{DV}	Time to Data Valid	NR ⁽¹⁾		

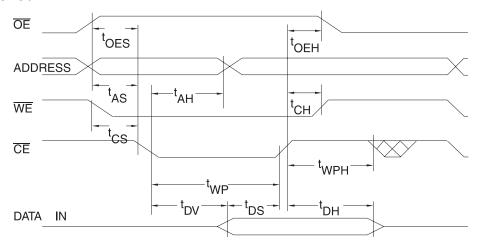
Note: 1. NR = No Restriction

15. AC Write Waveforms

15.1 WE Controlled



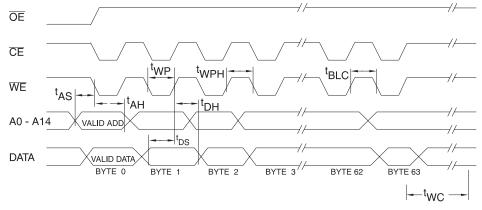
15.2 **CE** Controlled



16. Page Mode Characteristics

Symbol	Parameter		Min	Max	Units
		AT28C256		10	ms
t _{WC}	Write Cycle Time (option available)	AT28C256F		3	ms
t _{AS}	Address Setup Time		0		ns
t _{AH}	Address Hold Time		50		ns
t_{DS}	Data Setup Time		50		ns
t _{DH}	Data Hold Time		0		ns
t_{WP}	Write Pulse Width		100		ns
t _{BLC}	Byte Load Cycle Time			150	μs
t _{WPH}	Write Pulse Width High		50		ns

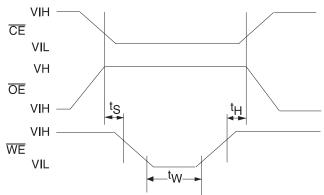
17. Page Mode Write Waveforms⁽¹⁾⁽²⁾



Notes: 1. A6 through A14 must specify the same page address during each high to low transition of WE (or CE).

2. \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.

18. Chip Erase Waveforms

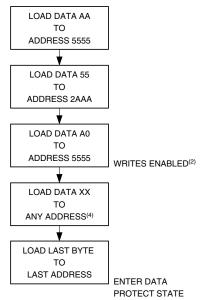


 $t_S = t_H = 5 \mu sec (min.)$ $t_W = 10 msec (min.)$ $V_H = 12.0V \pm 0.5V$





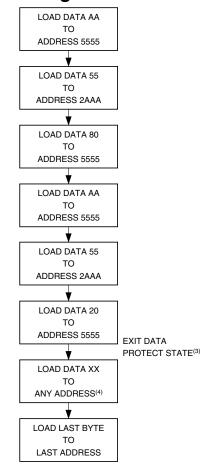
19. Software Data Protection Enable Algorithm⁽¹⁾



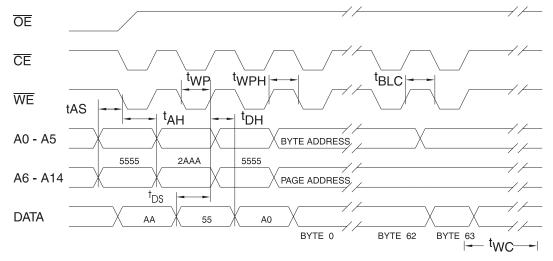
Notes: 1. Data Format: I/O7 - I/O0 (Hex); Address Format: A14 - A0 (Hex).

- Write Protect state will be activated at end of write even if no other data is loaded.
- Write Protect state will be deactivated at end of write period even if no other data is loaded.
- 4. 1 to 64 bytes of data are loaded.

20. Software Data Protection Disable Algorithm⁽¹⁾



21. Software Protected Write Cycle Waveforms⁽¹⁾⁽²⁾



Notes: 1. A6 through A14 must specify the same page address during each high to low transition of WE (or CE) after the software code has been entered.

2. \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.

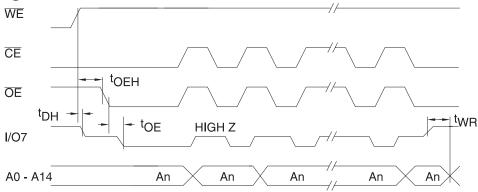
22. Data Polling Characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	0			ns
t _{OEH}	OE Hold Time	0			ns
t _{OE}	ŌĒ to Output Delay ⁽²⁾				ns
t _{WR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See "AC Read Characteristics" on page 6.

23. Data Polling Waveforms



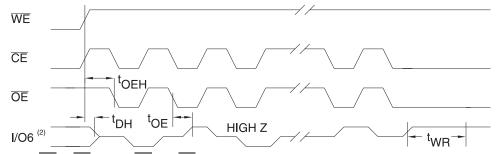
24. Toggle Bit Characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OEH}	OE Hold Time	10			ns
t _{OE}	\overline{OE} to Output Delay ⁽²⁾				ns
t _{OEHP}	OE High Pulse	150			ns
t _{WR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See "AC Read Characteristics" on page 6.

25. Toggle Bit Waveforms⁽¹⁾⁽²⁾⁽³⁾



Notes: 1. Toggling either \overline{OE} or \overline{CE} or both \overline{OE} and \overline{CE} will operate toggle bit.

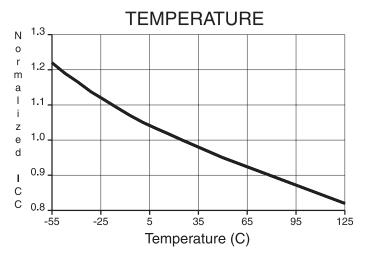
- 2. Beginning and ending state of I/O6 will vary.
- 3. Any address location may be used but the address should not vary.



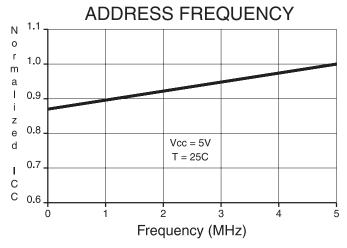


26. Normalized I_{CC} Graphs

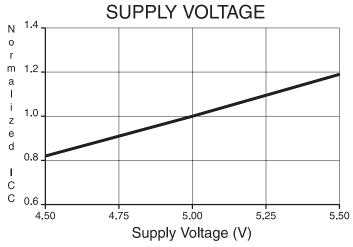
NORMALIZED SUPPLY CURRENT vs.



NORMALIZED SUPPLY CURRENT vs.



NORMALIZED SUPPLY CURRENT vs.



27. Ordering Information⁽²⁾

27.1 Standard Package

t _{ACC}	I _{CC} (mA)				
(ns)	Active	Standby	Ordering Code	Package	Operation Range
150	50	0.2	AT28C256(E,F)-15JI	32J	Industrial
			AT28C256(E,F)-15PI	28P6	(-40° C to 85° C)
			AT28C256(E,F)-15SI	28S	
			AT28C256(E,F)-15TI	28T	
		0.3	AT28C256(E,F)-15DM/883	28D6	Military/883C
			AT28C256(E,F)-15FM/883	28F	Class B, Fully Compliant
			AT28C256(E,F)-15LM/883	32L	
			AT28C256(E,F)-15UM/883	28U	(-55° C to 125° C)
200	50	0.3	AT28C256(E,F)-20DM/883	28D6	Military/883C
			AT28C256(E,F)-20FM/883	28F	•
			AT28C256(E,F)-20LM/883	32L	Class B, Fully Compliant
			AT28C256(E,F)-20UM/883	28U	(-55° C to 125° C)
250	50	0.3	AT28C256(E,F)-25DM/883	28D6	
			AT28C256(E,F)-25FM/883	28F	Military/883C
			AT28C256(E,F)-25LM/883	32L	Class B, Fully Compliant
			AT28C256(E,F)-25UM/883	28U	(-55° C to 125° C)
			AT28C256(E,F)-35UM/883	28U	

	Package Type					
28D6	28-lead, 0.600" Wide, Non-windowed, Ceramic Dual Inline Package (Cerdip)					
28F	28-lead, Non-windowed, Ceramic Bottom-brazed Flat Package (Flatpack)					
32J	32-lead, Plastic J-leaded Chip Carrier (PLCC)					
32L	32-pad, Non-windowed, Ceramic Leadless Chip Carrier (LCC)					
28P6	28-lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)					
28\$	28-lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)					
28T	28-lead, Plastic Thin Small Outline Package (TSOP)					
28U	28-pin, Ceramic Pin Grid Array (PGA)					
W	Die					
	Options					
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms					
E	High Endurance Option: Endurance = 100K Write Cycles					
F	Fast Write Option: Write Time = 3 ms					





27.1 Standard Package (Continued)

t _{ACC}	I _{cc} ((mA)			
(ns)	Active	Standby	Ordering Code	Package	Operation Range
150 ⁽³⁾	50	0.3	5962-88525 16 UX 5962-88525 16 XX 5962-88525 16 YX 5962-88525 16 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55° C to 125° C)
			5962-88525 15 UX 5962-88525 15 XX 5962-88525 15 YX 5962-88525 15 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55° C to 125° C)
			5962-88525 14 UX 5962-88525 14 XX 5962-88525 14 YX 5962-88525 14 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55° C to 125° C)

	Package Type					
28D6	28-lead, 0.600" Wide, Non-windowed, Ceramic Dual Inline Package (Cerdip)					
28F	28-lead, Non-windowed, Ceramic Bottom-brazed Flat Package (Flatpack)					
32J	32-lead, Plastic J-leaded Chip Carrier (PLCC)					
32L	32-pad, Non-windowed, Ceramic Leadless Chip Carrier (LCC)					
28P6	28-lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)					
28U	28-pin, Ceramic Pin Grid Array (PGA)					
W	Die					
	Options					
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms					
E	High Endurance Option: Endurance = 100K Write Cycles					
F	Fast Write Option: Write Time = 3 ms					

14

27.1 Standard Package (Continued)

t _{ACC}	I _{cc} ((mA)			
(ns)	Active	Standby	Ordering Code	Package	Operation Range
150 ⁽³⁾	50	0.3	5962-88525 08 UX	28U	Military/883C
			5962-88525 08 XX	28D6	Class B, Fully Compliant
			5962-88525 08 YX	32L	(-55° C to 125° C)
			5962-88525 08 ZX	28F	
			5962-88525 07 UX	28U	Military/883C
			5962-88525 07 XX	28D6	Class B, Fully Compliant
			5962-88525 07 YX	32L	(-55° C to 125° C)
			5962-88525 07 ZX	28F	
			5962-88525 06 UX	28U	Military/883C
			5962-88525 06 XX	28D6	Class B, Fully Compliant
			5962-88525 06 YX	32L	(-55° C to 125° C)
			5962-88525 06 ZX	28F	
200 ⁽³⁾	50	0.3	5962-88525 12 UX	28U	Military/883C
			5962-88525 12 XX	28D6	Class B, Fully Compliant
			5962-88525 12 YX	32L	(-55° C to 125° C)
			5962-88525 12 ZX	28F	
	50	0.3	5962-88525 04 UX	28U	Military/883C
			5962-88525 04 XX	28D6	Class B, Fully Compliant
			5962-88525 04 YX	32L	(-55° C to 125° C)
			5962-88525 04 ZX	28F	
250 ⁽³⁾	50	0.3	5962-88525 13 UX	28U	Military/883C
			5962-88525 13 XX	28D6	Class B, Fully Compliant
			5962-88525 13 YX	32L	(-55° C to 125° C)
			5962-88525 13 ZX	28F	
			5962-88525 11 UX	28U	Military/883C
			5962-88525 11 XX	28D6	Class B, Fully Compliant
			5962-88525 11 YX	32L	(-55° C to 125° C)
			5962-88525 11 ZX	28F	

	Package Type					
28D6	28-lead, 0.600" Wide, Non-windowed, Ceramic Dual Inline Package (Cerdip)					
28F	28-lead, Non-windowed, Ceramic Bottom-brazed Flat Package (Flatpack)					
32L	32-pad, Non-windowed, Ceramic Leadless Chip Carrier (LCC)					
28U	28-pin, Ceramic Pin Grid Array (PGA)					
W	Die					
	Options					
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms					
E	High Endurance Option: Endurance = 100K Write Cycles					
F	Fast Write Option: Write Time = 3 ms					





Standard Package (Continued) 27.1

t _{ACC}	I _{CC} (mA)				
(ns)	Active	Standby	Ordering Code	Package	Operation Range
250	50	0.3	5962-88525 05 UX	28U	Military/883C
			5962-88525 05 XX	28D6	Class B, Fully Compliant
			5962-88525 05 YX	32L	(-55° C to 125° C)
			5962-88525 05 ZX	28F	
			5962-88525 03 UX	28U	Military/883C
			5962-88525 03 XX	28D6	Class B, Fully Compliant
			5962-88525 03 YX	32L	(-55° C to 125° C)
			5962-88525 03 ZX	28F	
300	50	0.3	5962-88525 10 UX	28U	Military/883C
			5962-88525 10 XX	28D6	Class B, Fully Compliant
			5962-88525 10 YX	32L	(-55° C to 125° C)
			5962-88525 10 ZX	28F	
	50	0.3	5962-88525 02 UX	28U	Military/883C
			5962-88525 02 XX	28D6	Class B, Fully Compliant
			5962-88525 02 YX	32L	(-55° C to 125° C)
			5962-88525 02 ZX	28F	
350	50	0.3	5962-88525 09 UX	28U	Military/883C
			5962-88525 09 XX	28D6	Class B, Fully Compliant
			5962-88525 09 YX	32L	(-55° C to 125° C)
			5962-88525 09 ZX	28F	
	50	0.3	5962-88525 01 UX	28U	Military/883C
			5962-88525 01 XX	28D6	Class B, Fully Compliant
			5962-88525 01 YX	32L	(-55° C to 125° C)
			5962-88525 01 ZX	28F	

- Notes: 1. Electrical specifications for these speeds are defined by Standard Microcircuit Drawing 5962-88525.
 - 2. See "Valid Part Numbers" on page 18.
 - 3. SMD specifies Software Data Protection feature for device type, although Atmel product supplied to every device type in the SMD is 100% tested for this feature.

	Package Type					
28D6	28-lead, 0.600" Wide, Non-windowed, Ceramic Dual Inline Package (Cerdip)					
28F	28-lead, Non-windowed, Ceramic Bottom-brazed Flat Package (Flatpack)					
32L	32-pad, Non-windowed, Ceramic Leadless Chip Carrier (LCC)					
28U	28-pin, Ceramic Pin Grid Array (PGA)					
W	Die					
	Options					
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms					
E	High Endurance Option: Endurance = 100K Write Cycles					
F	Fast Write Option: Write Time = 3 ms					

27.2 Green Package Option (Pb/Halide-free)

t _{ACC}	I _{CC} (mA)				
(ns)	Active	Standby	Ordering Code	Package	Operation Range
150	50	0.2	AT28C256(E, F)-15JU	32J	Industrial
			AT28C256(E, F)-15PU	28P6	(-40° C to 85° C)
			AT28C256(E, F)-15SU	28S	
			AT28C256(E, F)-15TU	28T	

Package Type						
32J	32-lead, Plastic J-leaded Chip Carrier (PLCC)					
28P6	28-lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)					
28\$	28-lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)					
28T	28-lead, Plastic Thin Small Outline Package (TSOP)					
	Options					
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms					
F	Fast Write Option: Write Time = 3 ms					





28. Valid Part Numbers

The following table lists standard and green Atmel products that can be ordered.

Device Numbers	Speed	Package and Temperature Combinations
AT28C256	15	JI, JU, PI, PU, SI, SU, TI, TU, DM/883, FM/883, LM/883, UM/883
AT28C256E	15	JI, JU, PI, PU, SI, SU, TI, TU, DM/883, FM/883, LM/883, UM/883
AT28C256F	15	JI, JU, PI, PU, SI, SU, TI, TU, DM/883, FM/883, LM/883, UM/883
AT28C256	20	DM/883, FM/883, LM/883, UM/883
AT28C256E	20	DM/883, FM/883, LM/883, UM/883
AT28C256F	20	DM/883, FM/883, LM/883, UM/883
AT28C256	25	DM/883, FM/883, LM/883, UM/883
AT28C256E	25	DM/883, FM/883, LM/883, UM/883
AT28C256F	25	DM/883, FM/883, LM/883, UM/883

29. Die Products

Reference Section: Parallel EEPROM Die Products

Packaging Information

29.1 28D6 - Cerdip

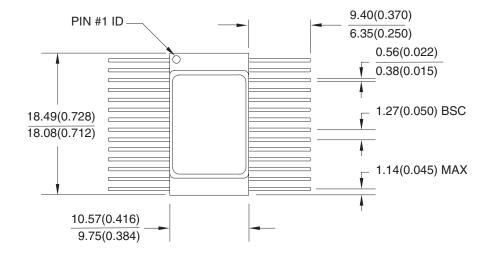
Dimensions in Millimeters and (Inches). Controlling dimension: Inches. MIL-STD 1835 D-10 Config A (Glass Sealed) 37.85(1.490) 36.58(1.440) PIN 15.49(0.610) 12.95(0.510) 33.02(1.300) REF -5.72(0.225) 0.127(0.005)MIN MAX **SEATING** PLANE 1.52(0.060) 5.08(0.200) 0.38(0.015) 3.18(0.125) 0.66(0.026) 1.65(0.065) 0.36(0.014) 1.14(0.045) 2.54(0.100)BSC 15.70(0.620) 15.00(0.590) 0°~ 15° REF 0.46(0.018) 0.20(0.008) 17.80(0.700) MAX 10/23/03 DRAWING NO. TITLE REV. 2325 Orchard Parkway 28D6, 28-lead, 0.600" Wide, Non-windowed, 28D6 В San Jose, CA 95131 Ceramic Dual Inline Package (Cerdip)

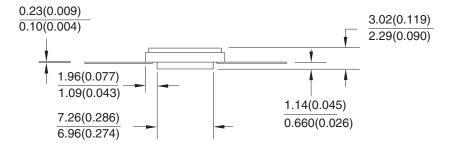




29.2 28F - Flatpack

Dimensions in Millimeters and (Inches). Controlling dimension: Inches. MIL-STD 1835 F-12 Config B



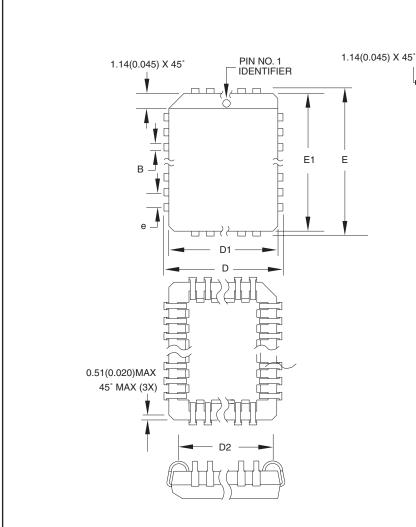


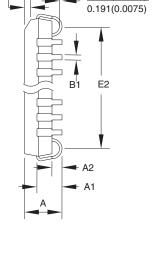
10/21/03

2325 Orchard Parkway San Jose, CA 95131 **TITLE 28F**, 28-lead, Non-windowed, Ceramic Bottom-brazed Flat Package (FlatPack)

DRAWING NO. 28F REV.

29.3 32J - PLCC





0.318(0.0125)

COMMON DIMENSIONS

(Unit of Measure = mm)

0)/44001	BAINI	NOM	MAN	NOTE
SYMBOL	MIN	NOM	MAX	NOTE
Α	3.175	_	3.556	
A1	1.524	-	2.413	
A2	0.381	_	_	
D	12.319	_	12.573	
D1	11.354	_	11.506	Note 2
D2	9.906	_	10.922	
Е	14.859	_	15.113	
E1	13.894	_	14.046	Note 2
E2	12.471	_	13.487	
В	0.660	_	0.813	
B1	0.330	-	0.533	
е		1.270 TYF)	

10/04/01

Notes:

- 1. This package conforms to JEDEC reference MS-016, Variation AE.
- Dimensions D1 and E1 do not include mold protrusion.
 Allowable protrusion is .010"(0.254 mm) per side. Dimension D1 and E1 include mold mismatch and are measured at the extreme material condition at the upper or lower parting line.
- 3. Lead coplanarity is 0.004" (0.102 mm) maximum.

2325 Orchard Parkway San Jose, CA 95131

IIILE		
32J , 32-lead,	Plastic J-leaded Chip Carrier (PLCC)	

DRAWING NO. REV.
32J B



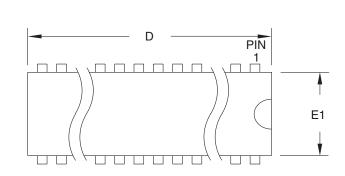


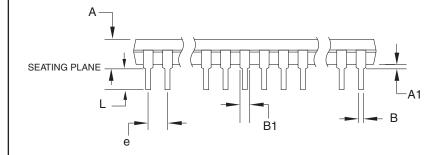
29.4 32L - LCC

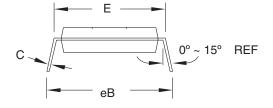
Dimensions in Millimeters and (Inches). Controlling dimension: Inches. MIL-STD 1835 C-12 11.63(0.458) 11.23(0.442) 2.54(0.100) 2.16(0.085) 14.22(0.560) 13.72(0.540) 1.91(0.075) 1.40(0.055) PIN 1 1.40(0.055) 1.14(0.045) INDEX CORNER 2.41(0.095) 1.91(0.075) $\frac{0.635(0.025)}{0.381(0.015)}X~45^{\circ}$ $\frac{0.305(0.012)}{0.178(0.007)} \text{RADIUS}$ 10.16(0.400) BSC 0.737(0.029) 0.533(0.021) 1.02(0.040) X 45° 1.27(0.050) TYP -2.16(0.085) 7.62(0.300) BSC 1.65(0.065) 10/21/03 DRAWING NO. REV. TITLE 2325 Orchard Parkway 32L, 32-pad, Non-windowed, Ceramic Lid, Leadless Chip 32L В San Jose, CA 95131 Carrier (LCC)

AT28C256

29.5 28P6 - PDIP







Notes:

- 1. This package conforms to JEDEC reference MS-011, Variation AB.
- 2. Dimensions D and E1 do not include mold Flash or Protrusion. Mold Flash or Protrusion shall not exceed 0.25 mm (0.010").

Parkway

95131

COMMON DIMENSIONS

(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
Α	_	_	4.826	
A1	0.381	_	_	
D	36.703	_	37.338	Note 2
Е	15.240	_	15.875	
E1	13.462	_	13.970	Note 2
В	0.356	_	0.559	
B1	1.041	_	1.651	
L	3.048	_	3.556	
С	0.203	_	0.381	
eB	15.494	_	17.526	
е		2.540 TYF)	

09/28/01

AMEL	2325 Orchard	
	San Jose, CA	

TITLE $\textbf{28P6}, \, \textbf{28-lead} \,\, (0.600 \text{"}/15.24 \,\, \text{mm Wide}) \,\, \text{Plastic Dual Inline Package} \,\, (\text{PDIP})$ DRAWING NO. REV. 28P6

В





29.6 28S - SOIC

Dimensions in Millimeters and (Inches). Controlling dimension: Millimeters. 0.51(0.020) 0.33(0.013) 7.60(0.2992) 10.65(0.419) 7.40(0.2914) $\overline{10.00(0.394)}$ PIN 1 ID 1.27(0.50) BSC TOP VIEW 18.10(0.7125) 2.65(0.1043) 17.70(0.6969) 2.35(0.0926) 0.30(0.0118) 0.10(0.0040) SIDE VIEWS 0° ~ 8° 0.32(0.0125) 0.23(0.0091) 1.27(0.050) 0.40(0.016) 8/4/03 DRAWING NO. TITLE REV. 2325 Orchard Parkway

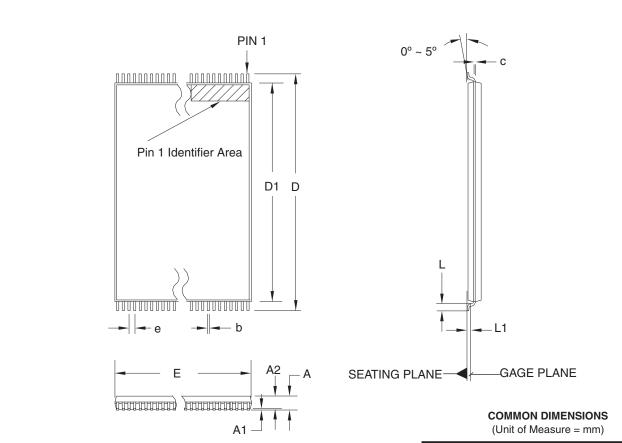
San Jose, CA 95131

28S, 28-lead, 0.300" Body, Plastic Gull Wing Small Outline (SOIC) JEDEC Standard MS-013

28S

В

29.7 28T - TSOP



Notes:

- 1. This package conforms to JEDEC reference MO-183.
- 2. Dimensions D1 and E do not include mold protrusion. Allowable protrusion on E is 0.15 mm per side and on D1 is 0.25 mm per side.
- 3. Lead coplanarity is 0.10 mm maximum.

(0 0				
SYMBOL	MIN	NOM	MAX	NOTE
Α	_	_	1.20	
A1	0.05	_	0.15	
A2	0.90	1.00	1.05	
D	13.20	13.40	13.60	
D1	11.70	11.80	11.90	Note 2
Е	7.90	8.00	8.10	Note 2
L	0.50	0.60	0.70	
L1	0.25 BASIC			
b	0.17	0.22	0.27	
С	0.10	_	0.21	
е	0.55 BASIC			

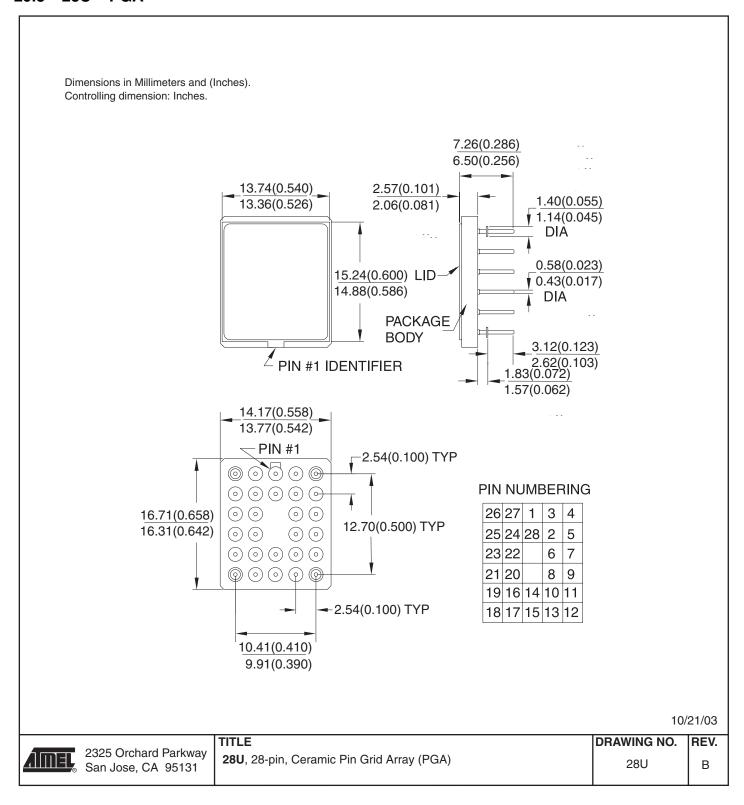
12/06/02

		DRAWING NO.	REV.
2325 Orchard Parkway San Jose, CA 95131	28T , 28-lead (8 x 13.4 mm) Plastic Thin Small Outline Package, Type I (TSOP)	28T	С





29.8 28U - PGA



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